

## High Temperature Silicon Carbide Power Schottky Diode

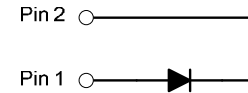
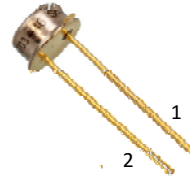
$V_{RRM}$	=	300 V
$I_F (T_C=25^\circ\text{C})$	=	4 A
$Q_C$	=	9 nC

### Features

- 300 V Schottky rectifier
- 210 °C maximum operating temperature
- Zero reverse recovery charge
- Superior surge current capability
- Positive temperature coefficient of  $V_F$
- Temperature independent switching behavior
- Lowest figure of merit  $Q_C/I_F$
- Available screened to Mil-PRF-19500

### Package

- RoHS Compliant



TO – 46

### Advantages

- High temperature operation
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Industry's lowest reverse recovery charge
- Industry's lowest device capacitance
- Ideal for output switching of power supplies
- Best in class reverse leakage current at operating temperature

### Applications

- Down Hole Oil Drilling
- Geothermal Instrumentation
- Solenoid Actuators
- General Purpose High-Temperature Switching
- Amplifiers
- Solar Inverters
- Switched-Mode Power Supply (SMPS)
- Power Factor Correction (PFC)

### Maximum Ratings at $T_j = 210^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	$V_{RRM}$		300	V
Continuous forward current	$I_F$	$T_C = 25^\circ\text{C}$	4	A
Continuous forward current	$I_F$	$T_C \leq 180^\circ\text{C}$	2	A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 180^\circ\text{C}$	4	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	10	A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\ \mu\text{s}$	65	A
$I^2t$ value	$\int I^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	0.5	$\text{A}^2\text{S}$
Power dissipation	$P_{tot}$	$T_C = 25^\circ\text{C}$	64	W
Operating and storage temperature	$T_j, T_{stg}$		-55 to 210	$^\circ\text{C}$

### Electrical Characteristics at $T_j = 210^\circ\text{C}$ , unless otherwise specified

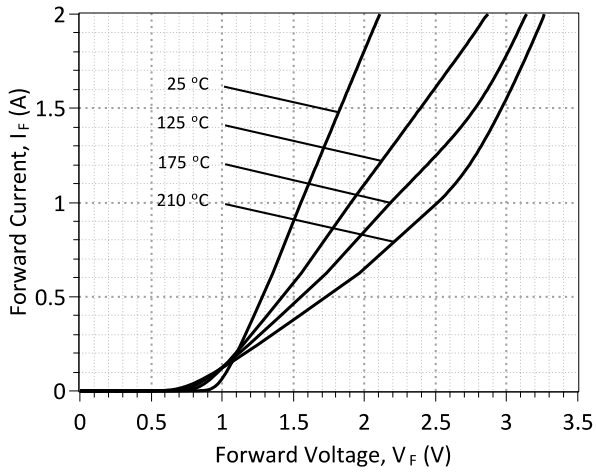
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	$V_F$	$I_F = 1\text{ A}, T_j = 25^\circ\text{C}$		1.6		V
		$I_F = 1\text{ A}, T_j = 210^\circ\text{C}$		2.6		
Reverse current	$I_R$	$V_R = 300\text{ V}, T_j = 25^\circ\text{C}$		1	5	$\mu\text{A}$
		$V_R = 300\text{ V}, T_j = 210^\circ\text{C}$		5	50	
Total capacitive charge	$Q_C$	$I_F \leq I_{F,MAX}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $T_j = 210^\circ\text{C}$		9		nC
Switching time	$t_s$	$V_R = 300\text{ V}$		< 17		ns
Total capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$		76		pF
		$V_R = 300\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$		15		

### Thermal Characteristics

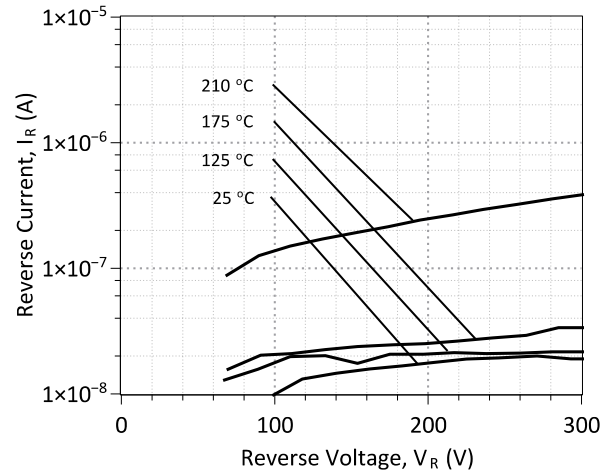
Thermal resistance, junction - case	$R_{thJC}$	5.55	$^\circ\text{C}/\text{W}$
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### Mechanical Properties

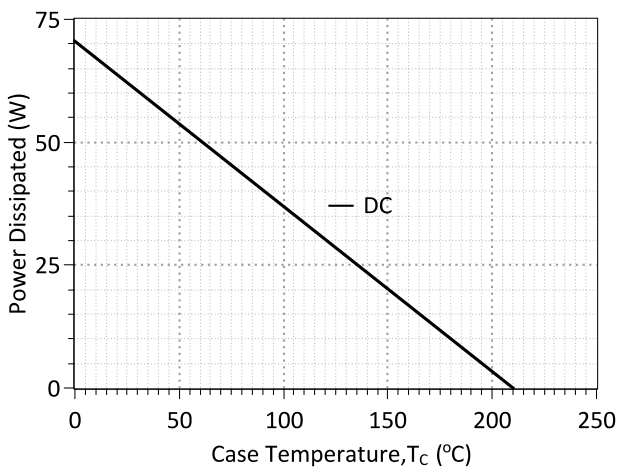
Mounting torque	M	0.6	Nm
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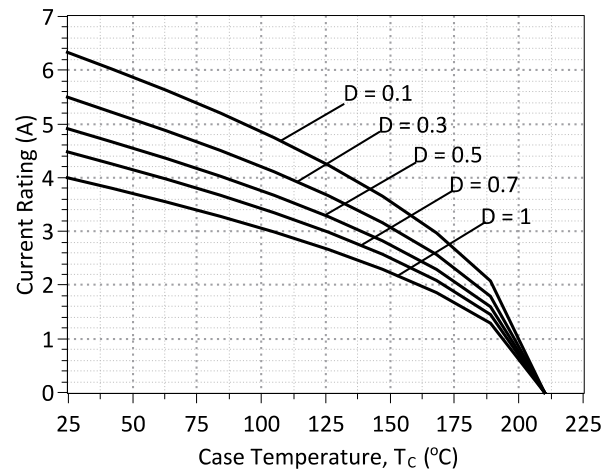
**Figure 1: Typical Forward Characteristics**



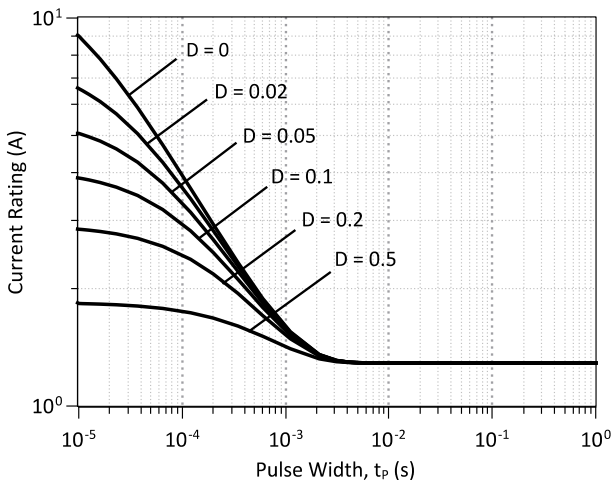
**Figure 2: Typical Reverse Characteristics**



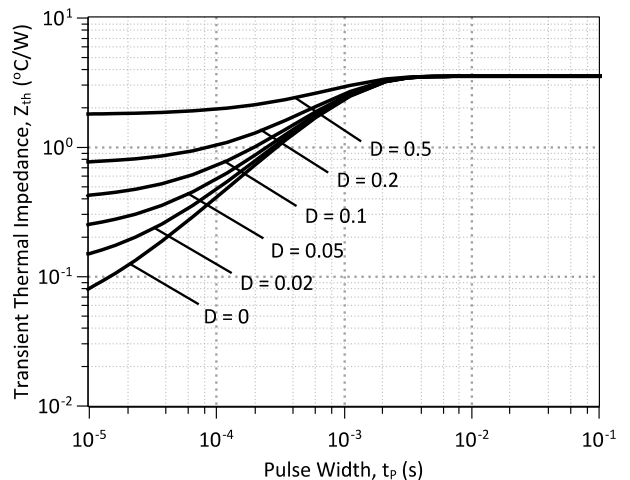
**Figure 3: Power Derating Curve**



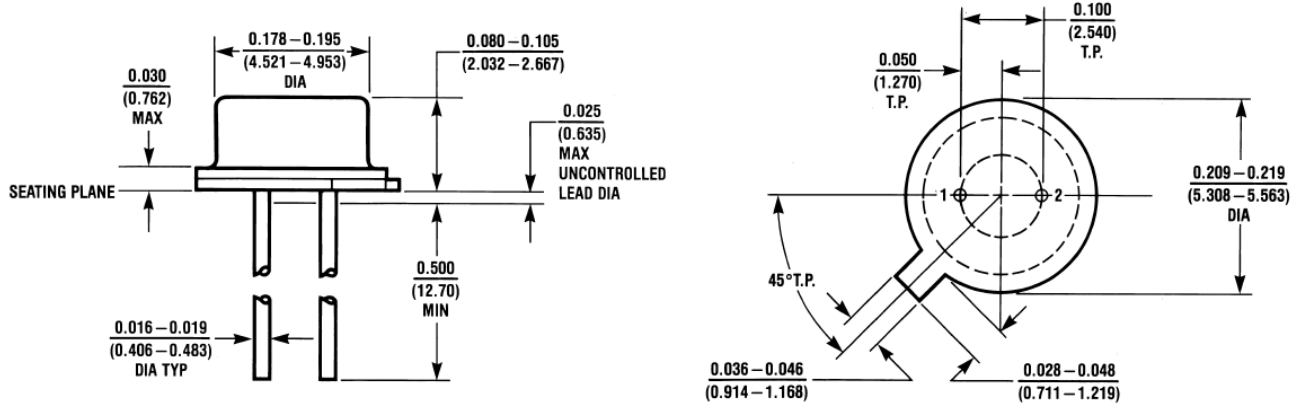
**Figure 4: Current Derating Curves ( $D = t_p/T$ ,  $t_p = 400 \mu s$ )  
(Considering worst case  $Z_{th}$  conditions)**



**Figure 5: Current vs Pulse Duration Curves at  $T_C = 190 \text{ }^\circ\text{C}$**



**Figure 6: Transient Thermal Impedance**

**Package Dimensions:**
**TO-46**
**PACKAGE OUTLINE**

**NOTE**

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

**Revision History**

Date	Revision	Comments	Supersedes
2014/08/29	0	Initial release	

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## SPICE Model Parameters

This is a secure document. Copy this code from the SPICE model PDF file on our website into a SPICE software program for simulation of the GB02SHT03-46.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      29-AUG-2014   $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2014 GeneSiC Semiconductor Inc.
*      ALL RIGHTS RESERVED
*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB02SHT03-46 SPICE Model
*
.SUBCKT GB02SHT03ANODE KATHODE
D1 ANODE KATHODE GB02SHT03_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB02SHT03_PIN; Call the PiN Diode Model
.MODEL GB02SHT03_25C D
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+ TRS1    0.0057       TRS2    2.40E-05
+ N       1            IKF     322
+ EG      1.2          XTI     3
+ CJO     9.12E-11     VJ      0.371817384
+ M       1.527759838  FC      0.5
+ TT      1.00E-10     BV      300
+ IBV     1.00E-03     VPK     300
+ IAVE    2            TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
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+ N       5            IKF     800
+ EG      3.23         XTI     -14
+ FC      0.5          TT      0
+ BV      300          IBV     1.00E-03
+ VPK     300          IAVE    2
+ TYPE    SiC_PiN
.ENDS
*
*      End of GB02SHT03 SPICE Model
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